



SFT1423 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		500	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		2	A
Drain Current (PW≤10μs)	I _{DP}	PW≤10μs, duty cycle≤1%	10	A
Allowable Power Dissipation	P _D		1.0	W
		T _c =25°C	20	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =10mA, V _{GS} =0V	500			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =400V, V _{GS} =0V			100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =1A	1.1	1.9		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =1A, V _{GS} =10V		3.8	4.9	Ω
	R _{DS(on)2}	I _D =0.5A, V _{GS} =4V		3.9	5	Ω

Marking : T1423

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SFT1423

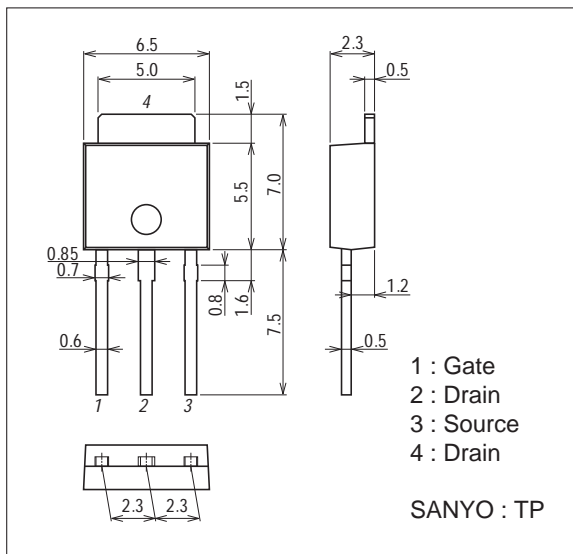
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	$V_{DS}=30V, f=1MHz$		175		pF
Output Capacitance	Coss	$V_{DS}=30V, f=1MHz$		32		pF
Reverse Transfer Capacitance	Crss	$V_{DS}=30V, f=1MHz$		6		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		7.4		ns
Rise Time	t_r	See specified Test Circuit.		8.8		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		42		ns
Fall Time	t_f	See specified Test Circuit.		27		ns
Total Gate Charge	Qg	$V_{DS}=200V, V_{GS}=10V, I_D=2A$		8.7		nC
Gate-to-Source Charge	Qgs	$V_{DS}=200V, V_{GS}=10V, I_D=2A$		1.1		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=200V, V_{GS}=10V, I_D=2A$		2.9		nC
Diode Forward Voltage	VSD	$I_S=2A, V_{GS}=0V$		0.9	1.2	V

Package Dimensions

unit : mm (typ)

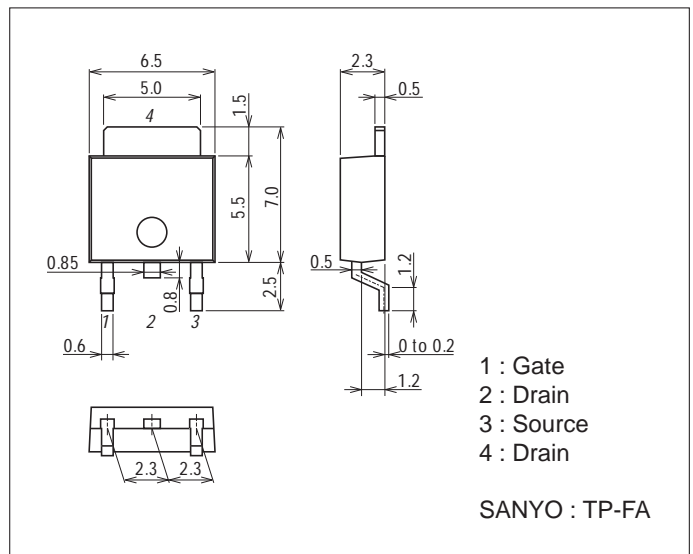
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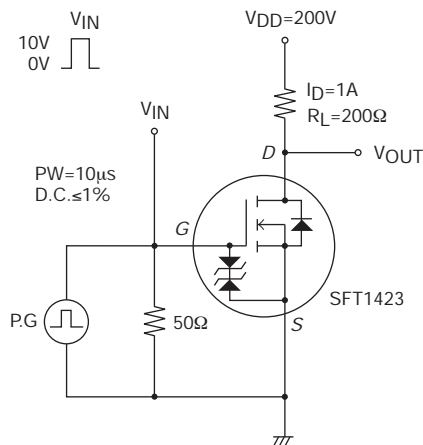
Package Dimensions

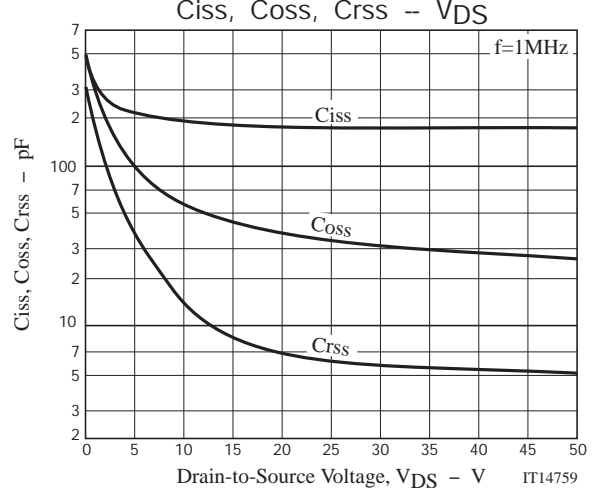
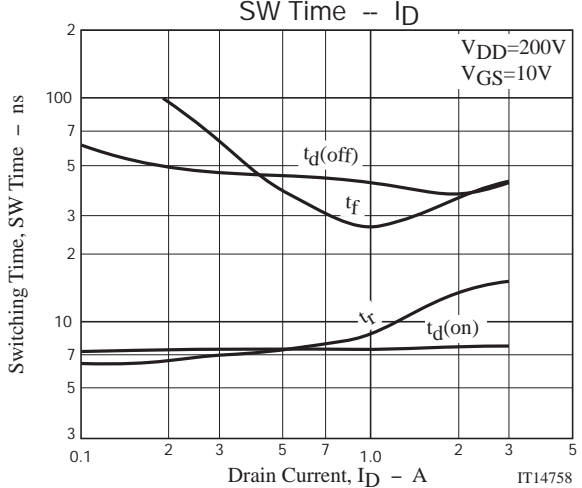
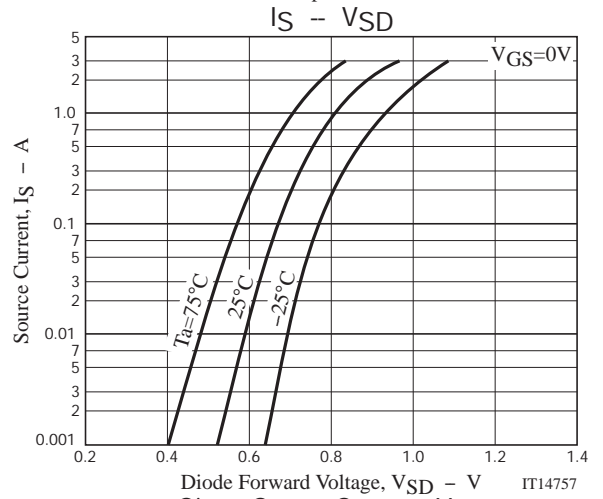
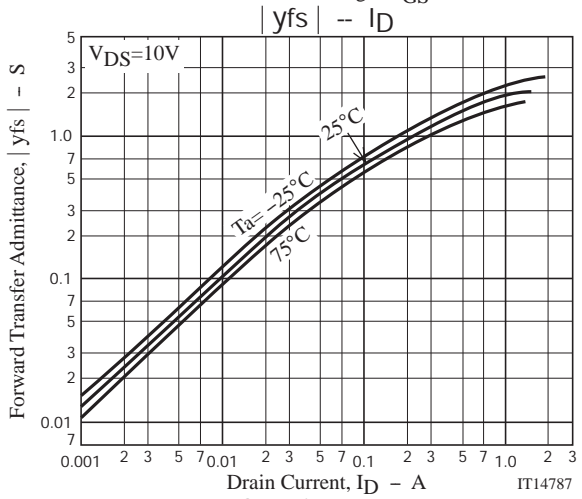
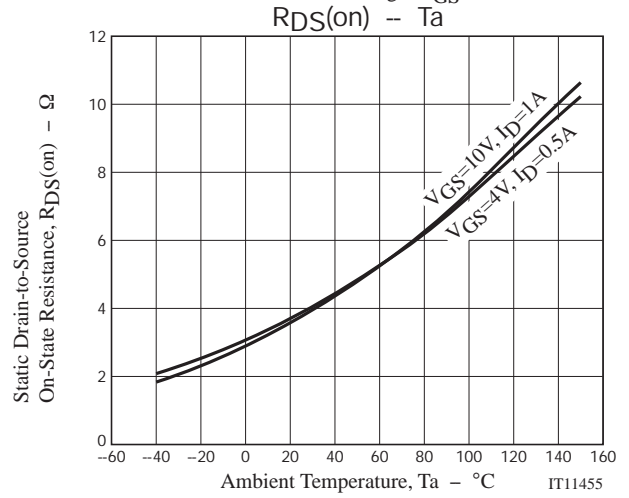
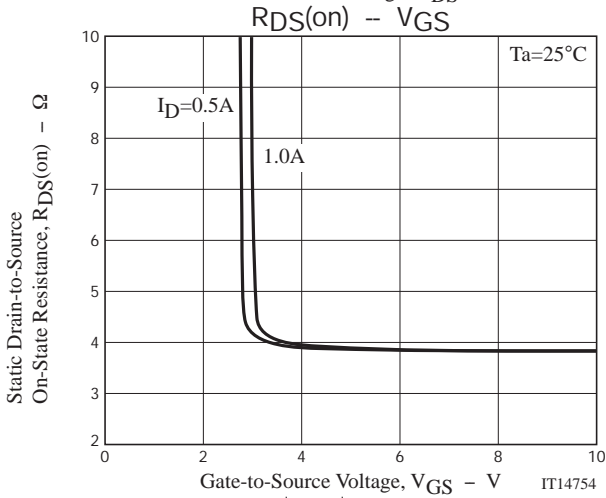
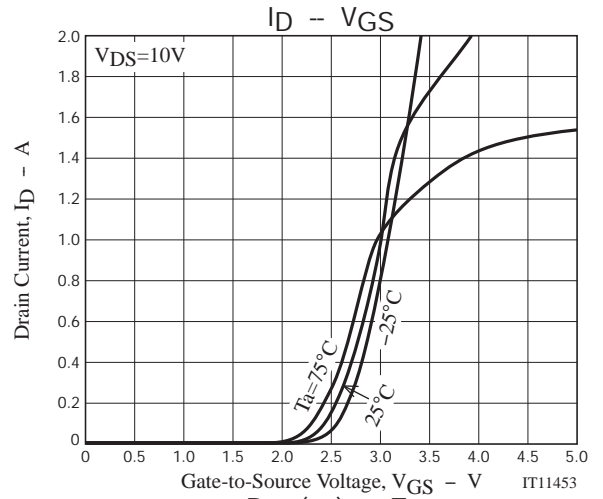
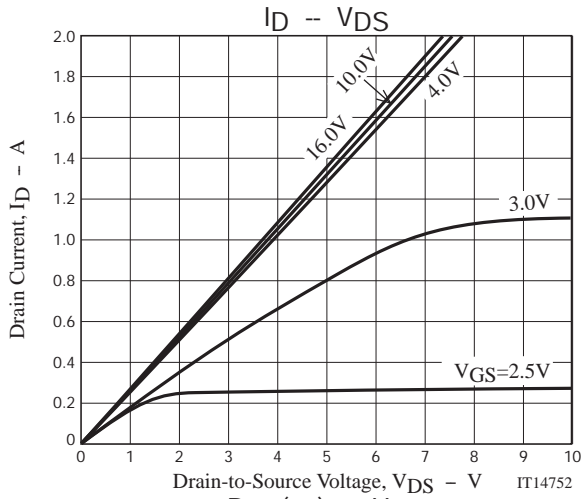
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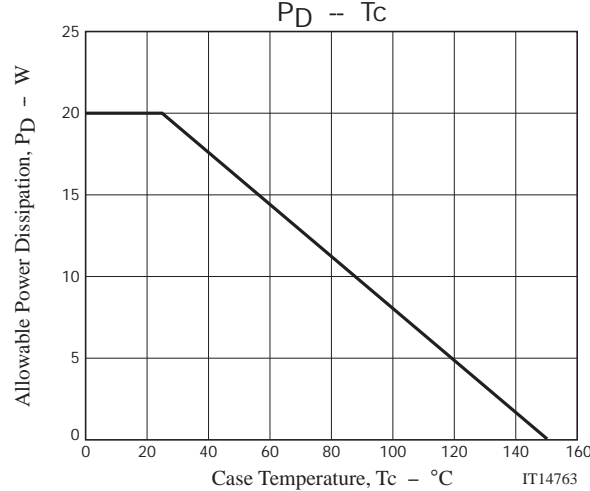
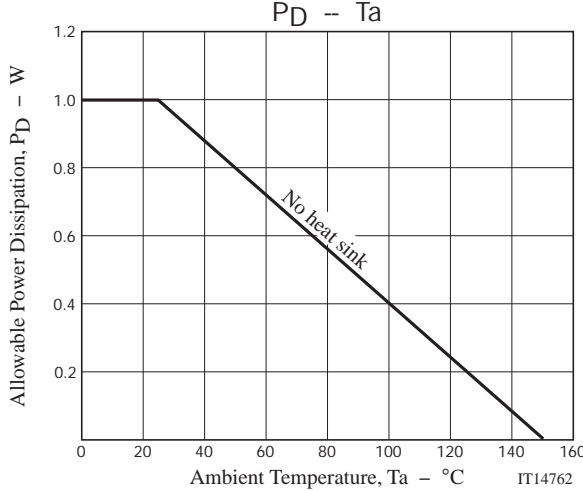
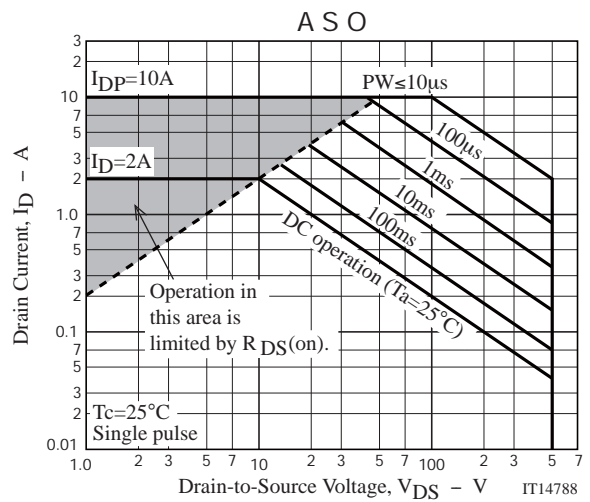
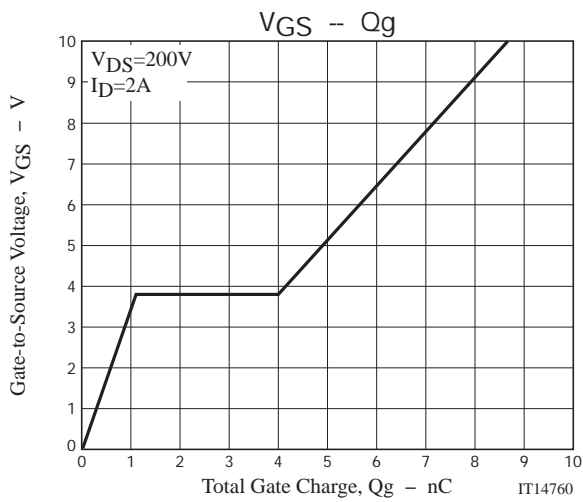
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Switching Time Test Circuit







Note on usage : Since the SFT1423 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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